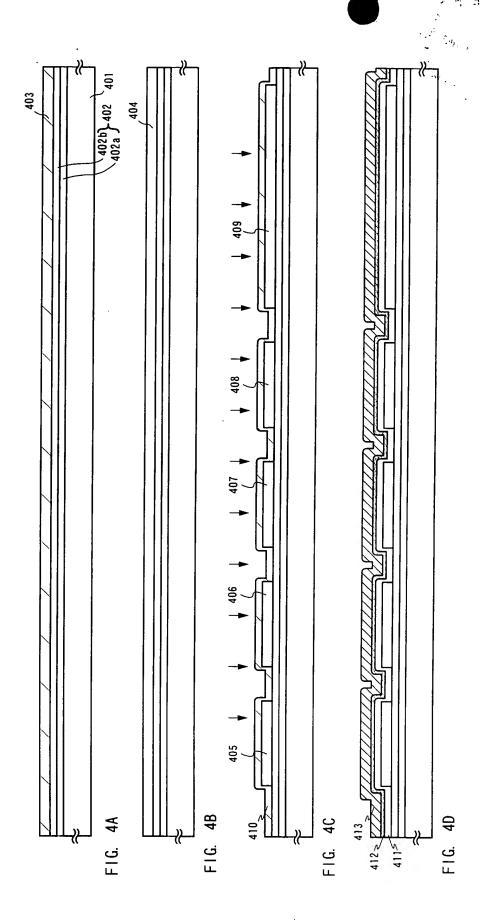
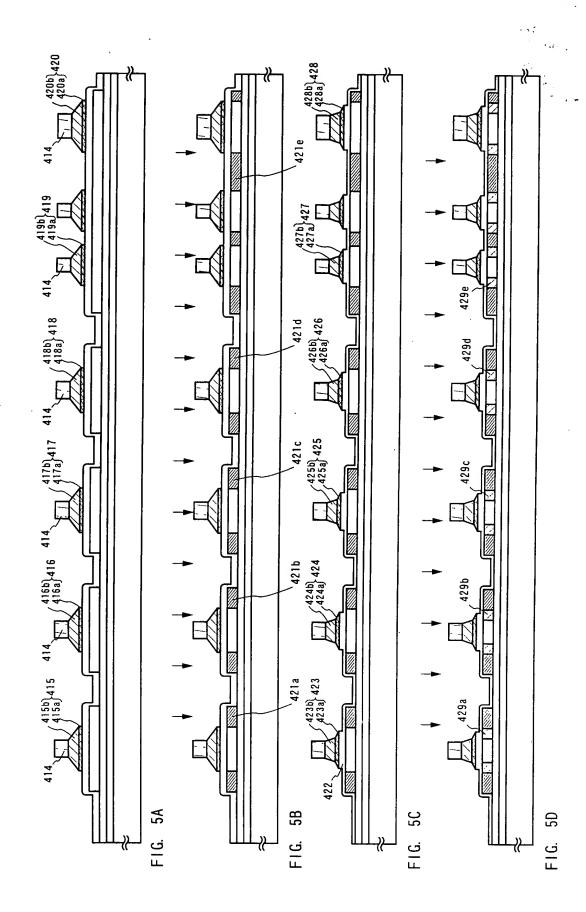
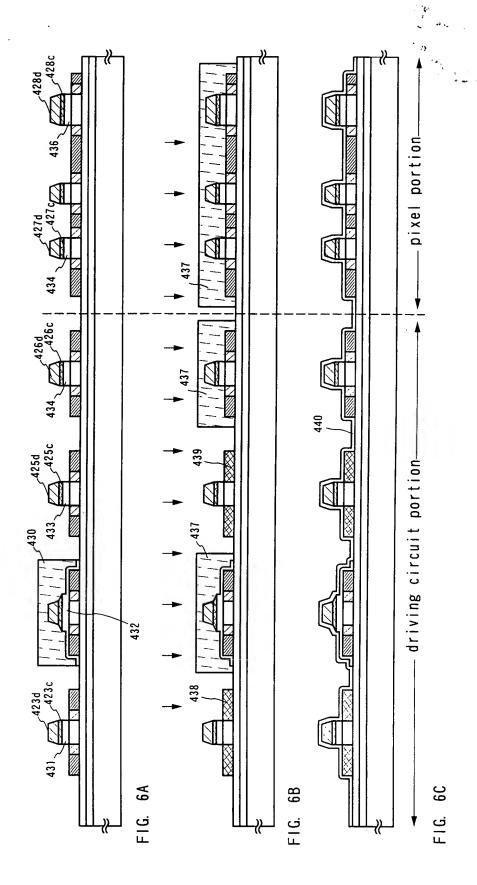


FIG. 3B







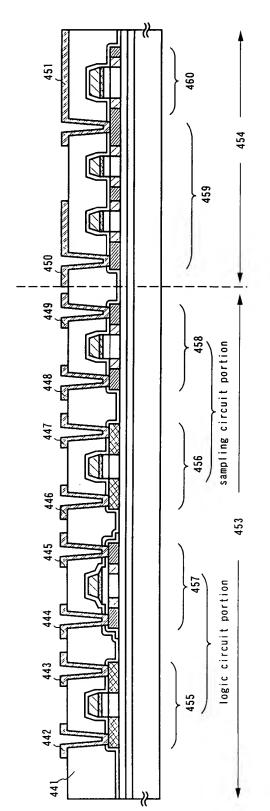


FIG.

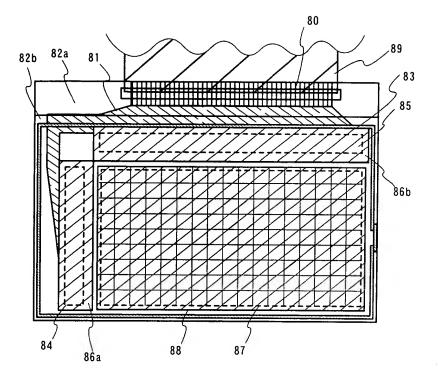


FIG. 8

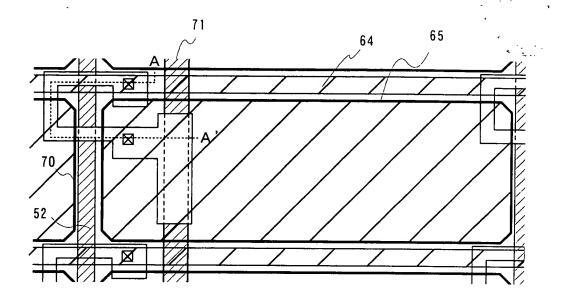


FIG. 9A

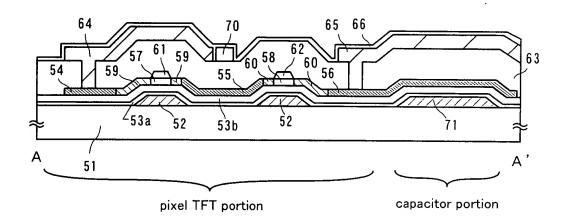
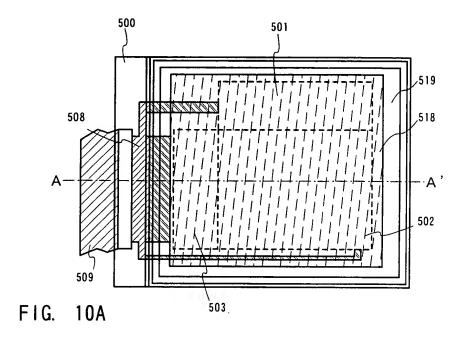
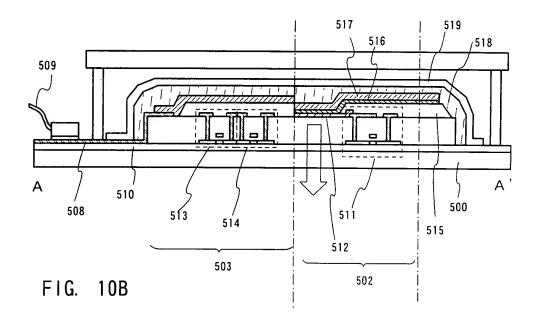


FIG. 9B





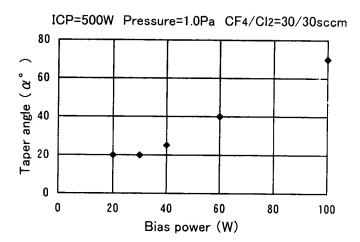


FIG. 11 Dependence of taper angle on bias power.

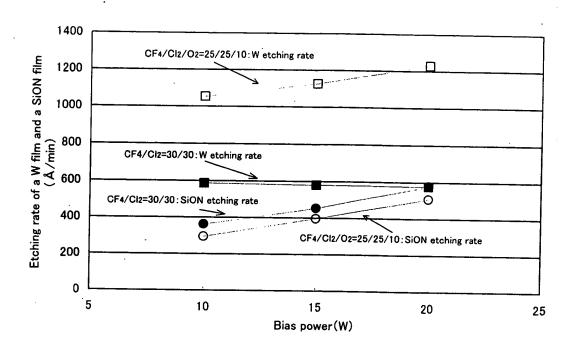


Fig. 12 Dependence of an etching rate of a W film and an SiON film on bias power.

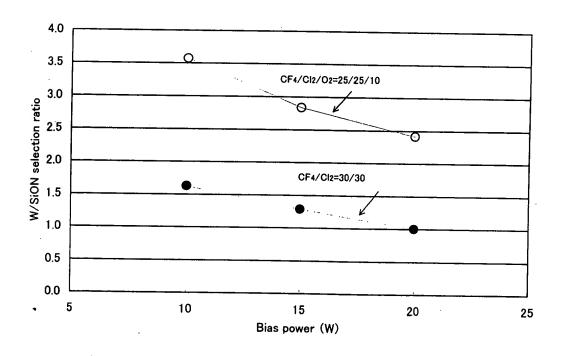


Fig. 13 Dependence of a selection ratio between a W film and an SiON film on a bias power.

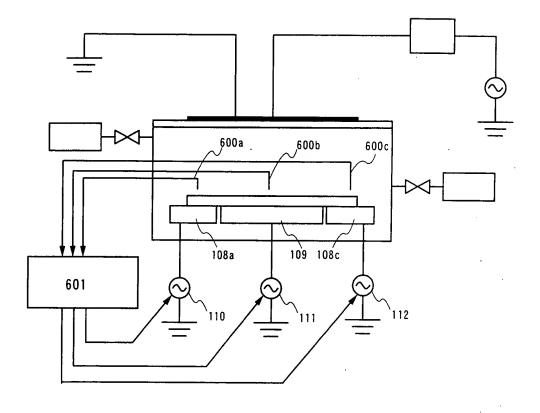


FIG. 14

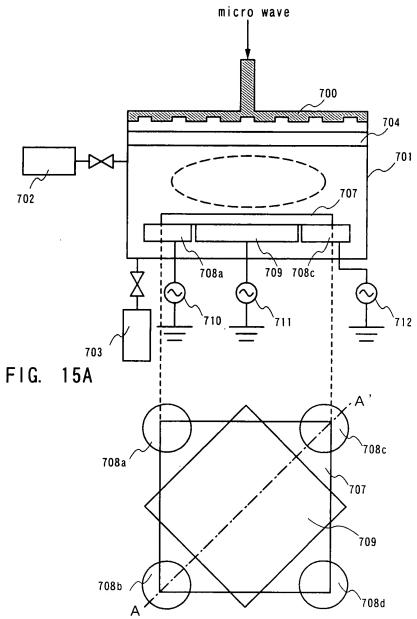


FIG. 15B

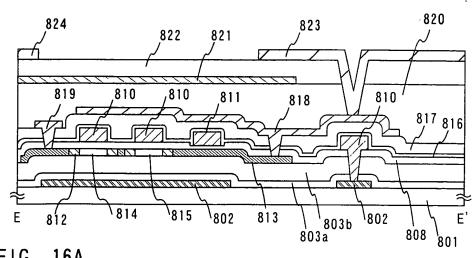


FIG. 16A

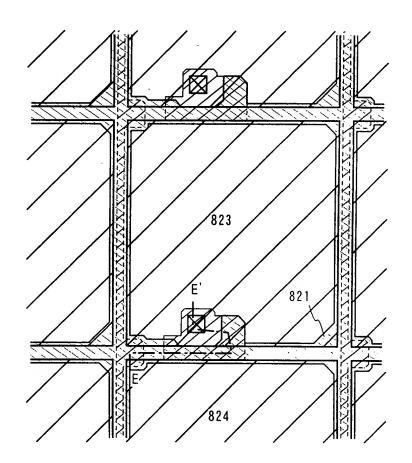


FIG. 16B

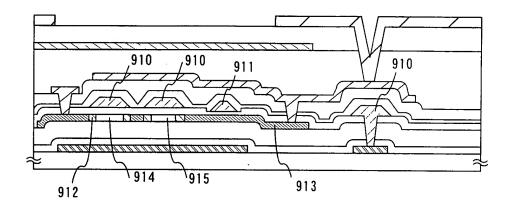
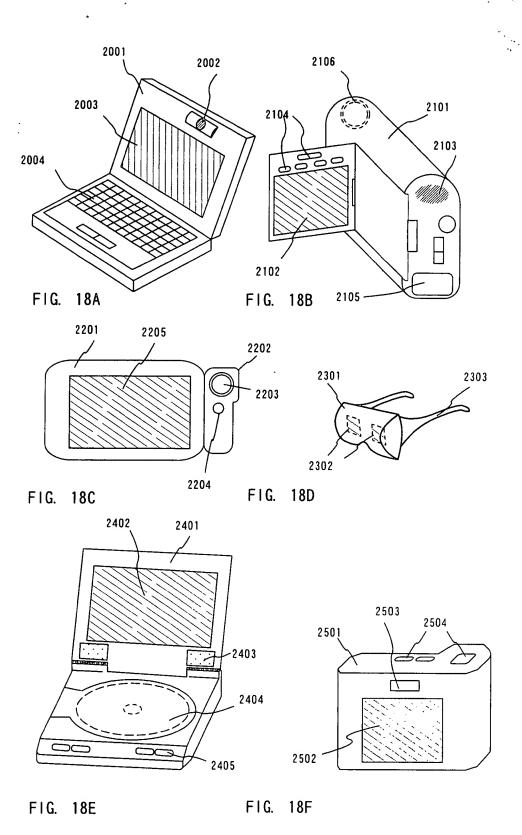


FIG. 17



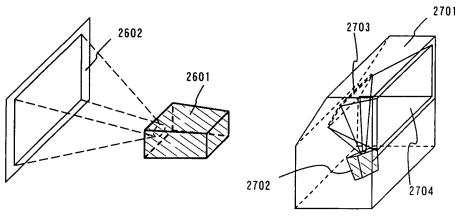


FIG. 19A

FIG. 19B

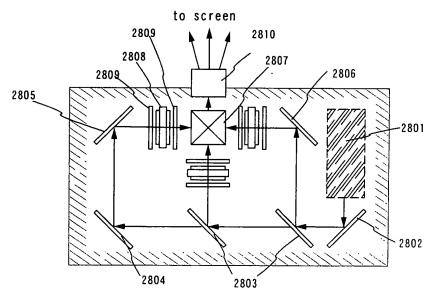


FIG. 19C

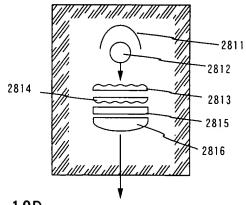
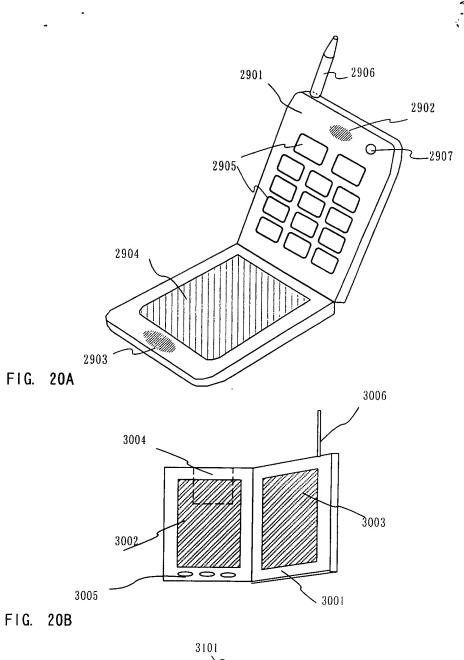
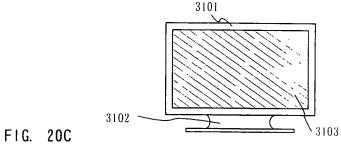


FIG. 19D





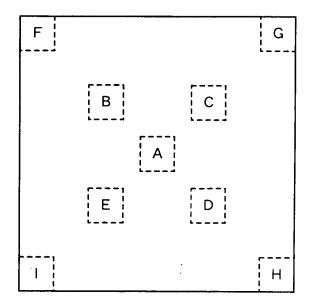


FIG. 21A

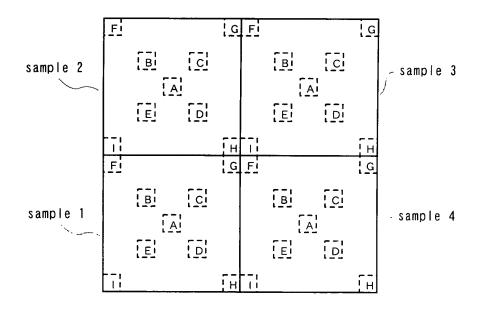


FIG. 21B